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cont.
--25. The semiconductor device according to claim 22, wherein the gate electrode includes a multi-layer structure having a low resistance conductive film.--

--26. The semiconductor device according to claim 25, wherein the low resistance conductive film includes at least one of a transition metal, a transition metal silicide, and a transition metal nitride film.--

--27. The semiconductor device according to claim 25, wherein the multi-layer structure is provided with a polysilicon film in between the germanium film and the low resistance conductive film.--

REMARKS

Claims 17-27 are pending in this application. By this Amendment, claims 1-16 are cancelled without prejudice to or disclaimer of the subject matter contained therein and claims 17-27 are added.

None of the applied art discloses the claimed invention as recited in independent claims 17 and 22.

In view of the foregoing amendments and remarks, Applicants submit that this application is in condition for allowance.

Should the Examiner believe that anything further would be desirable in order to place this application in better condition for allowance, the Examiner is invited to contact Applicants' undersigned representative at the telephone number listed below.

Respectfully submitted,



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Date: February 26, 2003

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